

**AMENDMENTS TO THE CLAIMS:**

Claims 1 and 2 are amended to differently recite the invention and claim 5 is canceled without prejudice or disclaimer of the subject matter therein. Claims 1-4 are currently pending. This listing of claims will replace all prior versions, and listings, of claims in the application.

Claim 1 (Currently Amended): A UV sensor comprising:

an incident light window constituting part of the wall of a container; and

a pin-type photodiode disposed inside said container and employed for photoelectrically converting the light that was transmitted through said incident light window,

wherein

said incident light window is composed of ~~Kovar glass~~ borosilicate glass, ~~[[and]]~~

said pin-type photodiode comprises a photoabsorption layer formed from  $\text{In}_x\text{Ga}_{(1-x)}\text{N}$  ( $0 < x < 1$ ) between an n-type nitride semiconductor layer and a p-type nitride semiconductor layer,

and

each energy gap of said n-type nitride semiconductor layer and p-type nitride semiconductor layer is equal to or larger than the energy gap of said photoabsorption layer.

Claim 2 (Currently Amended): The UV sensor according to claim 1, wherein said incident light window composed of ~~Kovar glass is formed to have~~ borosilicate glass has a thickness ~~[[of]]~~ equal to or greater than 200  $\mu\text{m}$  ~~or more~~.

Claim 3 (Original): The UV sensor according to claim 1, wherein the composition ratio  $x$  of the  $\text{In}_x\text{Ga}_{(1-x)}\text{N}$  in said photoabsorption layer is  $0 < x < 0.05$ .

Claim 4 (Original): The UV sensor according to claim 1, wherein the detection sensitivity of said light with a wavelength of 405 nm is not more than 1/100 of the detection sensitivity of said light with a wavelength of 365 nm.

Claim 5 (Canceled).